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CCS H83

SJ

INDUSTRY STANDARD OF THE PEOPLE'S REPUBLIC OF CHINA

SJ 21536-2018

Specification of gallium arsenide epitaxial wafer for microwave power devices and monolithic microwave integrated circuits

微波功率器件及集成电路用砷化镓外延片规范

(English Translation)

Issued by: Ministry of Industry and Information Technology

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1 Foreword

SJ 21536-2018 was issued by Ministry of Industry and Information Technology on 29 December 2018.

The SJ prefix, without a suffix, marks a mandatory standard: within its scope, compliance is required.

The document runs to 8 pages in English translation.

2 Scope Preview

SJ 21536-2018 is filed under Chinese Standard Classification H83, in the field of metallurgy.

This catalogue holds 1,191 other SJ standards without an ICS number.

In this catalogue, SJ standards carry edition years from 1965 to 2021.

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3 About this standard

Sector: Electronics Industry Standard

Issued by: Ministry of Industry and Information Technology

English translation: about 8 pages (approximate)

Chinese original: about 11,196 characters

4 Related standards

Standards on related subjects:

GB/T 25074-2017 - Solar-grade polycrystalline silicon

SJ/T 11488-2015 - Test method for measuring resistivity, hall coefficient and determining hall mobility in semi-insulating GaAs single crystals

YS/T 13-2015 - High pure germanium tetrachloride

SJ 21588-2021 - Indium Phosphide Crystal Ingot Cutting and Orientation Technology Requirements

SJ 21535-2018 - Specification of silicon carbide epitaxial wafer for power electronic device

SJ 21534-2018 - Specification of gallium nitride epitaxial wafer for microwave power transistor

5 Classification and status

Chinese Standard Classification (CCS): H 83

Prefix SJ: mandatory standard.

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